

EM513 THRU EM518

GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 1600 to 2000 Volts Forward Current - 1.0 Ampere

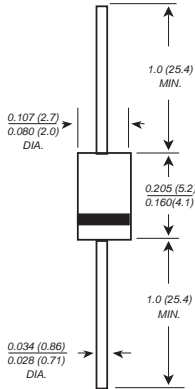
FEATURES

- ◆ The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- ◆ Construction utilizes void-free molded plastic technique
- ◆ Low reverse leakage
- ◆ High forward surge current capability
- ◆ High temperature soldering guaranteed:
250°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC DO-41 molded plastic body
Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026
Polarity: Color band denotes cathode end
Mounting Position: Any
Weight: 0.012 ounce, 0.33 grams

DO-41



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
 Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	EM513	EM516	EM518	UNITS
Maximum repetitive peak reverse voltage	V_{RRM}	1600	1800	2000	VOLTS
Maximum RMS voltage	V_{RMS}	1120	1260	1400	VOLTS
Maximum DC blocking voltage	V_{DC}	1600	1800	2000	VOLTS
Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=75^\circ\text{C}$	$I_{(AV)}$	1.0			Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	30.0			Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.1			Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=100^\circ\text{C}$	I_R	5.0 50.0			μA
Typical junction capacitance (NOTE 1)	C_J	15.0			pF
Typical thermal resistance (NOTE 2)	R_{qJA}	50.0			$^\circ\text{C/W}$
Operating junction and storage temperature range	T_J, T_{STG}	-65 to +175			$^\circ\text{C}$

Note: 1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 2. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted

RATINGS AND CHARACTERISTIC CURVES EM513 THRU EM518

